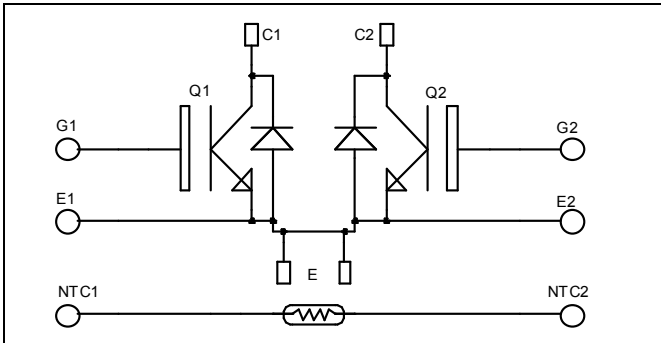


**Dual common source
Fast Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 1200V$
 $I_C = 50A @ T_c = 80^\circ C$**

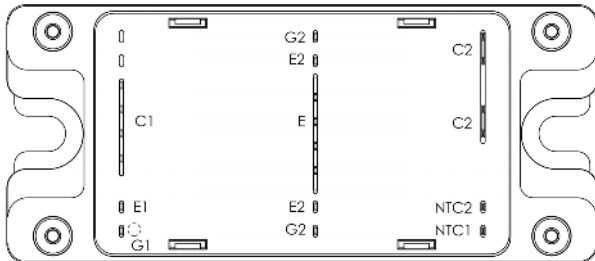


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	75
		$T_c = 80^\circ C$	50
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	277
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	100A @ 1150V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1200\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$		1.7 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

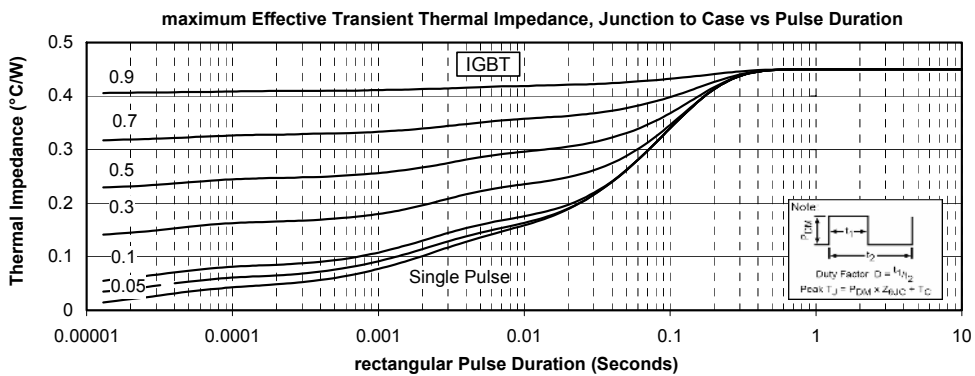
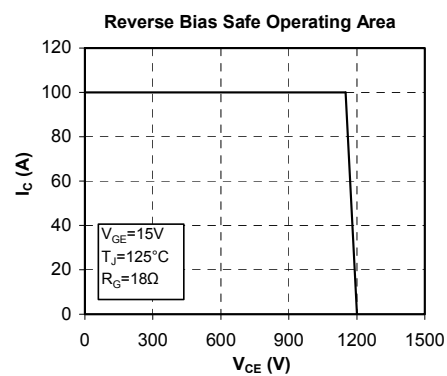
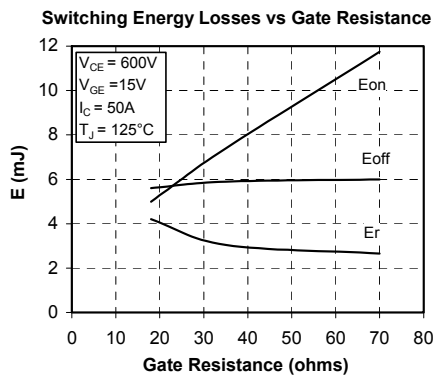
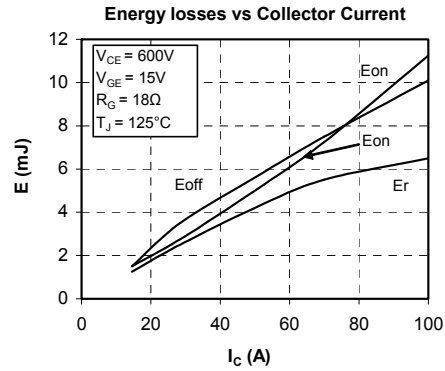
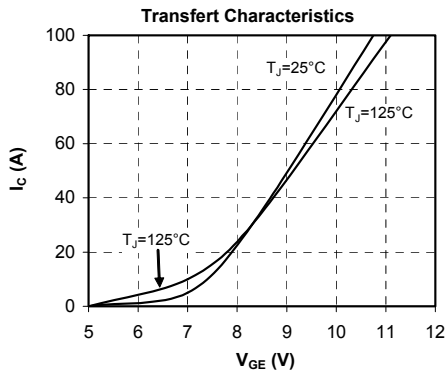
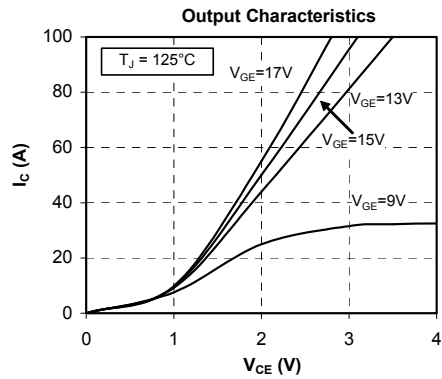
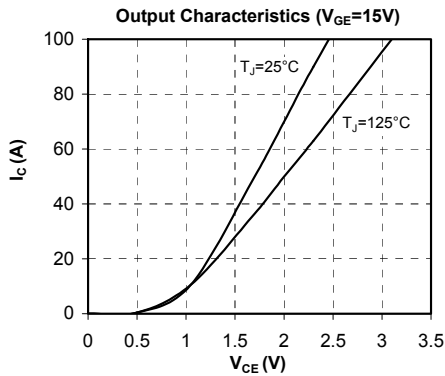
Dynamic Characteristics

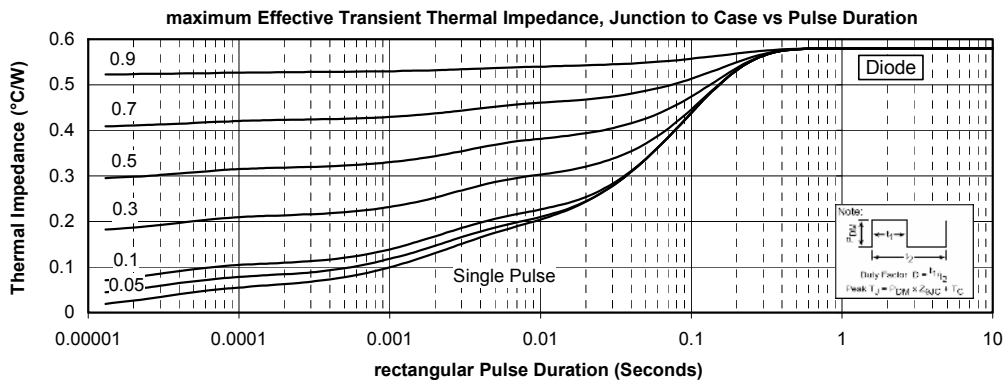
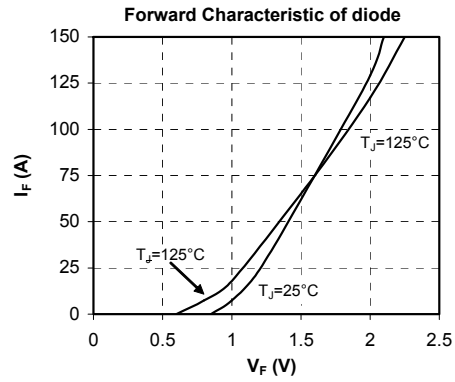
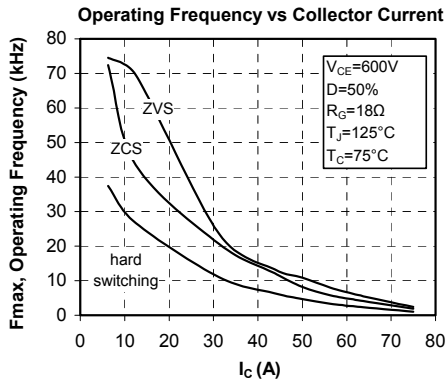
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		3600		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		190		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		160		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		90		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600\text{V}$ $I_C = 50\text{A}$		420		
T_f	Fall Time	$R_G = 18\ \Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		90		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600\text{V}$ $I_C = 50\text{A}$		520		
T_f	Fall Time	$R_G = 18\ \Omega$		90		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$		5		mJ
E_{off}	Turn-off Switching Energy	$I_C = 50\text{A}$ $R_G = 18\ \Omega$		5.5		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$			250 500	μA
I_F	DC Forward Current			50		A
V_F	Diode Forward Voltage	$I_F = 50\text{A}$		1.4 1.3	1.9	V
t_{rr}	Reverse Recovery Time			150 250		ns
Q_{rr}	Reverse Recovery Charge	$I_F = 50\text{A}$ $V_R = 600\text{V}$ $di/dt = 2000\text{A}/\mu\text{s}$		4.5 9		μC
E_r	Reverse Recovery Energy			2.1 4.2		mJ

Typical Performance Curve





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